HN1D03F

TOSHIBA Diode Silicon Epitaxial Planar Type

HN1D03F

Ultra High Speed Switching Application

Built in anode common and cathode common.

Unit 1

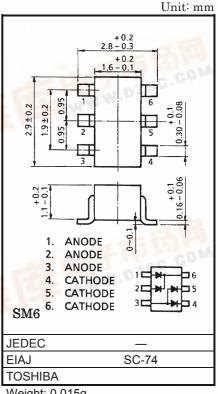
Q1, Q2: $V_{F(3)} = 0.90V$ (typ.) Low forward voltage Q1, Q2: $t_{rr} = 1.6ns$ (typ.) Fast reverse recovery time Small total capacitance Q1, Q2: $C_T = 0.9pF$ (typ.)

Unit 2

Low forward voltage Q3, Q4: $V_{F(3)} = 0.92V$ (typ.) • Fast reverse recovery time Q3, Q4: $t_{rr} = 1.6ns$ (typ.) Small total capacitance Q3, Q4: $C_T = 2.2pF$ (typ.)

Unit 1, Unit 2 Common Maximum Ratings (Ta = 25°C)

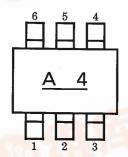
Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V _{RM}	85	V
Reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300 (*)	mA
Average forward current	I _O	100 (*)	mA
Surge current (10ms)	I _{FSM}	2 (*)	А
Power dissipation	Р	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~12 <mark>5</mark>	°C



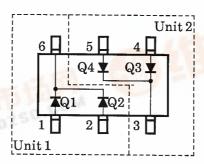
Weight: 0.015g

(*) This is the Maximum Ratings of single diode (Q1 or Q2 or Q3 or Q4). In the case of using Unit 1 and Unit 2 independently or simultaneously, the Maximum Ratings per diode is 75% of the single diode one.

Marking



Pin Assignment (Top View)





2001-06-07

 $(ROUT = 50\Omega)$

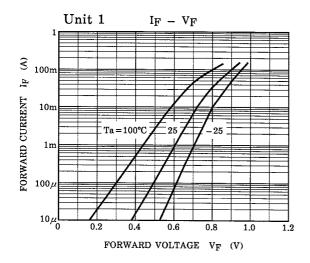
Fig.1 Reverse Recovery Time (t_{rr}) Test Circuit

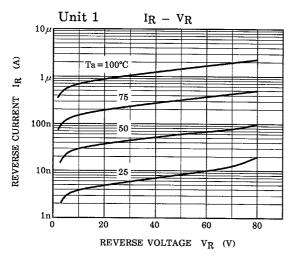
Unit 1 Electrical Characteristics (Q1, Q2, Common) (Ta = 25°C)

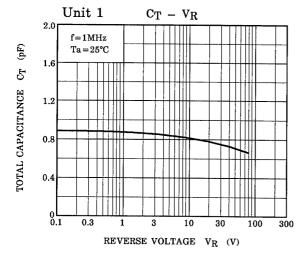
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V _{F (1)}	_	I _F = 1mA	ı	0.60	1	_
	V _{F (2)}	_	I _F = 10mA	١	0.72	١	V
	V _{F (3)}	_	I _F = 100mA	1	0.90	1.20	
Reverse current	I _{R (1)}	_	V _R = 30V	1	1	0.1	μА
	I _{R (2)}	_	V _R = 80V	1	1	0.5	
Total capacitance	C _T	_	V _R = 0, f = 1MHz		0.9	3.0	pF
Reverse recovery time	t _{rr}	_	I _F = 10mA (fig.1)	_	1.6	4.0	ns

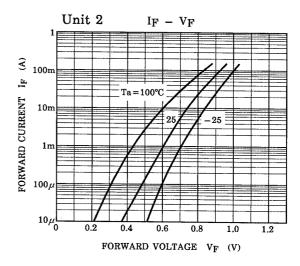
Unit 2 Electrical Characteristics (Q3, Q4, Common) (Ta = 25°C)

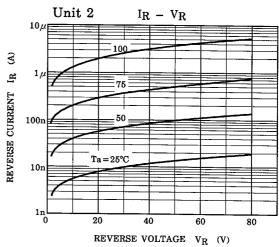
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V _{F (1)}	_	I _F = 1mA	1	0.61	_	
	V _{F (2)}	_	I _F = 10mA	-	0.74	-	V
	V _{F (3)}	_	I _F = 100mA	_	0.92	1.20	
Reverse current	I _{R (1)}	_	V _R = 30V	1		0.1	μΑ
	I _{R (2)}	_	V _R = 80V	-	_	0.5	
Total capacitance	C _T	_	V _R = 0, f = 1MHz	1	2.2	4.0	pF
Reverse recovery time	t _{rr}	_	I _F = 10mA (fig.1)	_	1.6	4.0	ns

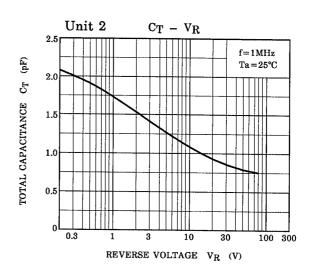












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